

isc Silicon NPN Power Transistor

MJ1800

DESCRIPTION

- High Collector-Emitter Voltage
- Good Linearity of h_{FE}

APPLICATIONS

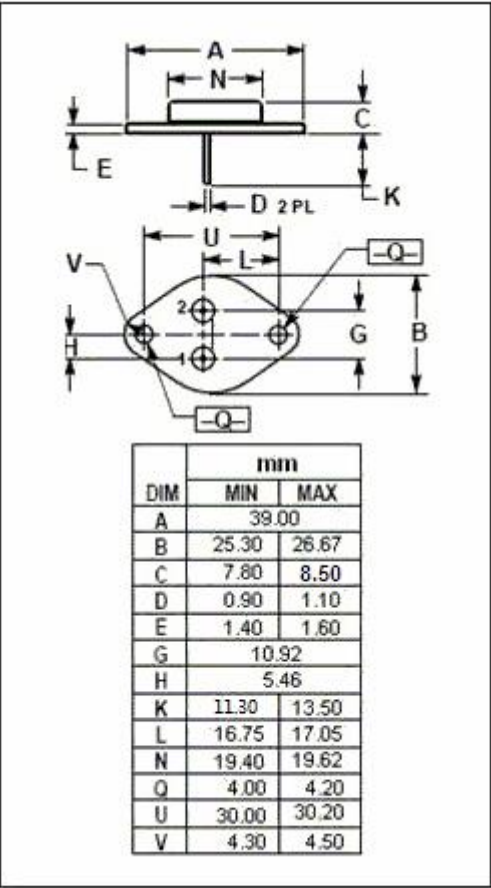
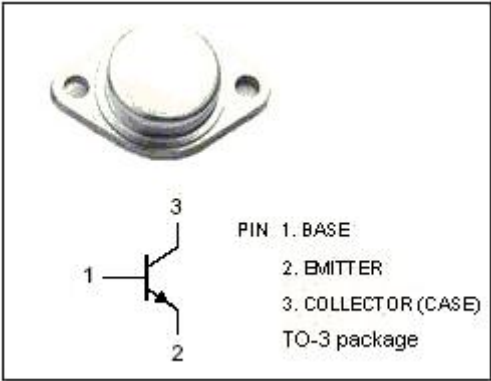
- Designed for use in vertical deflection amplifier circuits in television receivers.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEO}	Collector-Emitter Voltage	250	V
V_{CBO}	Collector- Base Voltage	500	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	5	A
P_C	Collector Power Dissipation@ $T_C=25^{\circ}\text{C}$	100	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.25	$^{\circ}\text{C/W}$



isc Silicon NPN Power Transistors**MJ1800****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 30\text{mA}; I_B = 0$	250			V
V_{CBO}	Collector Cutoff Current	$I_C = 1\text{mA}; I_E = 0$	500			V
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 5\text{V}; I_C = 0$			0.1	mA
h_{FE-1}	DC Current Gain	$I_C = 0.3\text{A}; V_{CE} = 5\text{V}$	35			
h_{FE-2}	DC Current Gain	$I_C = 0.4\text{A}; V_{CE} = 5\text{V}$	40		120	
h_{FE-1}/h_{FE-2}	Gain Linearity	/	0.95			